n-channel JFETs *designed for . . .*

- **VHF Amplifiers**
- **Oscillators**
- **Mixers**

Performance Curves NZA
See Section 4

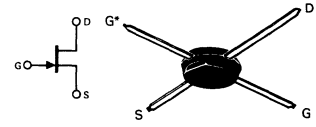
BENEFITS

- Hermetic Strip Line Package
- High Power Gain
  16 dB Typical at 105 MHz, Common-Gate
  11 dB Typical at 450 MHz, Common-Gate
- Low Noise Figure
  1.5 dB Typical at 105 MHz
  2.7 dB Typical at 450 MHz
- Wide Dynamic Range—Greater than 100 dB
- Worst Case Input Power Match (75 Ω) VSWR 1.25:1

ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage . . . . . -25 V
Gate Current . . . . . 20 mA
Total Device Dissipation . . . . . 175 mW
Derate . . . . . 1 mW/°C
Surface Temperature Range . . . . . -65°C to +200°C
Lead Temperature 1/16 From Case (max 10 Sec). . . . 300°C

OD-84
See Section 5



Note: G* is back Gate contact.

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic		J316 Min	J316 Max	J317 Min	J317 Max	Unit	Test Conditions	
1	STATIC	I_{GSS}	Gate Reverse Current		-1		-1	nA	V_{GS} = -15 V, V_{DS} = 0	
2					-1		-1	μA		T = 125°C
3		BV_{GSS}	Gate Source Breakdown Volt.	-25		-25		V	I_G = -1 μA, V_{DS} = 0	
4		$V_{GS(off)}$	Gate-Source Cutoff Voltage	-1	-4	-2.5	-6		V_{DS} = 10 V, I_D = 1 nA	
5		$V_{GS(f)}$	Gate-Source Forward Voltage		1		1		I_G = 10 mA, V_{DS} = 0	
6		I_{DSS}	Saturation Drain Current	12	30	24	60	mA	V_{DS} = 10 V, V_{GS} = 0 (Note 1)	
7	DYN	g_{fg}	Common-Gate Forward Transconductance	10	20	10	18	m mho	V_{DS} = 10 V, I_D = 10 mA	f = 1 kHz (Note 1)
8		g_{og}	Common-Gate Output Conductance		150		150	μ mho		
9		C_{gd}	Gate-Drain Capacitance		3		3	pF	V_{DS} = 10 V V_{GS} = -10 V	f = 1 MHz
10		C_{gs}	Gate-Source Capacitance		3		3			

NZA

NOTE:
1 Pulsed (test duration 2 mS)